



Over the last year the baseline design has seen only minor changes as the result of ongoing analyses or component/system-level tests:

1) For ultralightweight applications, the, 50  $\mu\text{m}$  (2 mil) carbon-loaded Kapton blanket substrate material was replaced by germanium-coated regular Kapton. The germanium coating has the same surface resistivity ( $\sim 10^8$  ohms/square) as the carbon-loaded material to permit grounding of the blanket substrate, to prevent electrostatic charge buildup from orbital plasma environments. It is also very resistant to atomic oxygen degradation (Banks, 1992), thus provides long term protection for low earth orbit (LEO) missions. It also has favorable thermophysical properties ( $\alpha/\epsilon \approx 0.5/0.8$ ), thereby reducing the heat loading and operating temperature of silicon solar cell circuits by up to  $15^\circ\text{C}$  from the earth's heating for LEO missions.

2.) Bypass diodes are integrated into the solar cell circuit design to ensure reliable power performance of the array when subjected to shadowing or as the result of cracked cells. The preliminary conservative requirement to have a thin wafer diode bypass every eight cells (Kurland, 1991) is currently under review based on a series of cell and circuit-level tests and analyses. Final guidelines won't be available for several months. However, it is clear that thin silicon cells will require protection using shunt diodes. Analysis and tests not funded under the APSA program also show this to be true for GaAs/Ge cells on a thin blanket substrate.

3) Under TRW discretionary funding a heavier blanket construction option was developed that replaces the single Kapton layer with a germanium-coated Kapton/graphite composite laminate. While heavier, the substrate eliminates the need for shunt diodes when using GaAs/Ge cells and may reduce the number of shunt diodes required for silicon solar cell circuits because of its heat conduction properties. A full size 3-panel solar panel assembly was constructed with thin large area GaAs/Ge cells and incorporated into the APSA wing. Stowed wing vibration tests successfully demonstrated the viability of the design concept.

## Panel-Level Activities

### SAMPLE Panel

In support of the NASA/LeRC Solar Array Module Plasma Interaction Experiment (SAMPIE) a series of test articles were fabricated consisting of  $15 \times 15$  cm ( $6 \times 6$  in.) square panels each with a 12-cell, soldered, series-interconnected circuit using  $2 \times 4$  cm, thin ( $\sim 75 \mu\text{m}$ ) silicon BSFR solar cells with  $100 \mu\text{m}$  thick AR/UV-coated ceria-doped microsheet covers. Both germanium-coated and carbon-load Kapton substrate test articles were constructed, all mounted on a thick aluminum plate. The SAMPLE program will investigate high voltage discharge characteristics on-board Shuttle in 1993 (Wald, 1991).

Plasma chamber testing of the coupons in preparation for the flight test indicate acceptable behavior in that the power loss from the plasma interaction with the weakly conducting blanket substrates is very small (Hillard, 1993).

### PASP-APEX Panel

In 1993, the Photovoltaic Array Space Power - Advanced PV and Electronics Experiment (PASP-APEX) will be launched for a 3 year elliptical near polar orbit mission ( $350 \times 1850$  km, 70 degree inclination) to measure high voltage discharge and radiation effects on advanced power designs (Burger, 1991). A small panel was fabricated consisting of germanium coated Kapton with a 12-cell, soldered, series-interconnected circuit using  $2.6 \times 5.1$  cm thin ( $\sim 65 \mu\text{m}$ ) silicon BSFR solar cells with  $50 \mu\text{m}$  thick AR/UV coated ceria-doped microsheet covers. The blanket section is supported in an aluminum frame.

### Thin Film GaAs Solar Cell Thermal Cycle Panel

The development of the pecked-film (also referred to as CLIFT) GaAs CCM by Kopin Corporation has the potential to improve the specific power and power density performance of the APSA array design by almost 40 percent, because the cell stack (cover-integrated cell) combines a mass less than a thin silicon cell stack with a photovoltaic conversion efficiency slightly greater than conventional thick GaAs/Ge cells. A  $2 \times 4$  cm cell, 5 to  $10 \mu\text{m}$  thick, when combined with a 50 to  $100 \mu\text{m}$  coverglass weighs from 170 to 270 mg and has a 28°C Ah40 efficiency of 18 to 19 percent, compared to 13.8 percent for a thin 290 to 390 mg silicon cell stack.

Two 12-cell solder-interconnected circuit panels using a  $50 \mu\text{m}$  germanium coated Kapton substrate (Fig. 4) were fabricated to evaluate the producibility of interconnected circuits and to evaluate long term thermal cycle performance. The thermal cycle tests, beginning in mid-1993, will be similar to those successfully performed on thin silicon cell panels (Scheiman, 1990), and will simulate 30 year GEO ( $-70$  to  $60^\circ\text{C}$ ) and 10 year LEO ( $-100$  to  $100^\circ\text{C}$ ) conditions.

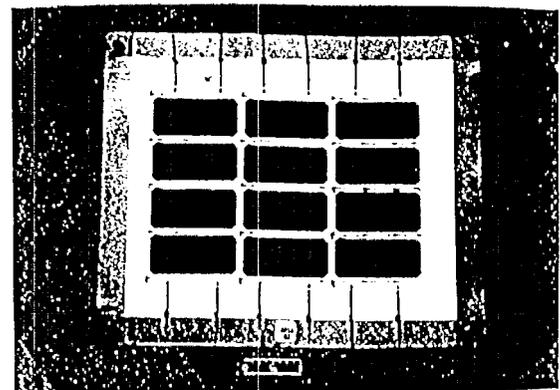


Fig. 4. Kopin pecked-film GaAs solar cell thermal cycle panel.

Several techniques were investigated to attach an interconnector to the thin gold contact pads that are supported by the DC93500 silicone adhesive layer that bonds the cover to the ultra-thin peeled-film cell. Thermosonic and ultrasonic bonding of gold ribbon/wire or aluminum wire, were attempted using micro-electronic wiring production techniques normally used for large-scale integrated circuits. The results were unsuccessful because the soft DC93500 adhesive support layer did not provide sufficient rigidity to permit intermetallic joining of the ribbon/wire to the contact pad. Other attempts were very successful when a rigid epoxy adhesive was substituted for the space-qualified silicone adhesive. However, since the epoxy adhesive is not space-qualified for solar cell stack applications, it was not used in the test panels. Instead a special inplane relief loop, silver-coated, Invar interconnector was developed and successfully joined to the gold contact pads with a tiny preform of low-temperature (143°C) indium-silver solder. A special electrode, slightly larger than the contact area, was used with low pressure (<200 mg) to minimize deformation of the contact pad or the chevron-shaped thermal relief fingers that connect the contact pad to the cell body (Fig. 5).

The results suggest that more development work is needed at the cell-level and at the circuit production level before cells of this type can be considered a viable, cost-effective or weight-effective option to current production "bulk" silicon or GaAs/Ge cells. However, this initial effort indicates the potential for future very high specific performance blanket designs.

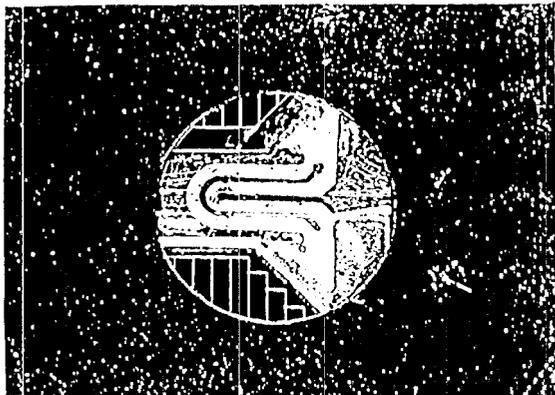


Fig. 5 Interconnection detail, Kopin peeled-film GaAs solar cell (viewed from cutout in panel substrate).

### Solar Cell and Circuit Reverse Bias Testing

A comprehensive coupon-level testing and analysis effort is in progress to determine weight- and cost-effective measures to ensure electrical integrity of the solar cell circuits against hot spots resulting from shadowing or cell breakage that can more readily occur for flexible blanket arrays. This activity represents a more in-depth effort than the 1991 effort which conservatively concluded thin wafer diodes would be needed for every eighth thin silicon solar cells.

Reverse bias characteristics and failure modes were measured on 200 thin BSFR silicon flight production cells from two domestic suppliers. Testing was done as a function of temperature, short circuit current level, repetitively pulsed reverse bias conditions, long duration reverse bias conditions, and charged particle irradiation conditions. Figs. 6 and 7 illustrate the wide variation in reverse breakdown voltage at ambient temperature. There were distinctive differences in the results from the two suppliers, one having a large spread in characteristics, with breakdown occurring from 10 to 65 volts at a current density level  $-1 \times I_{SC}$ ; and the other characterized by a narrower spread with high voltage (45 to 65 V) and low current density ( $-0.2 \times I_{SC}$ ). The difference in behavior is thought to be due to the methods used in producing the back surface field (boron diffusion doping versus ion-implantation). The effects of temperature level, pulsed or long duration reverse bias conditions or radiation on the reverse bias characteristics were small. Failure modes for both types of cells were either by shunting or shorting; open failures did not occur. Failure modes were observed via infrared thermography, with follow-up evaluation using scanning electron microscope and energy dispersive X-ray analyses on failure sites.

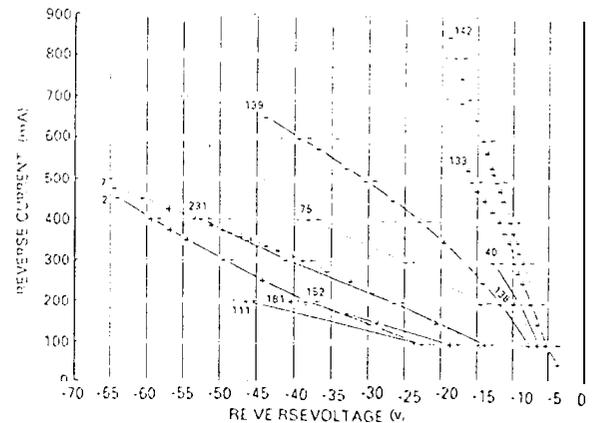
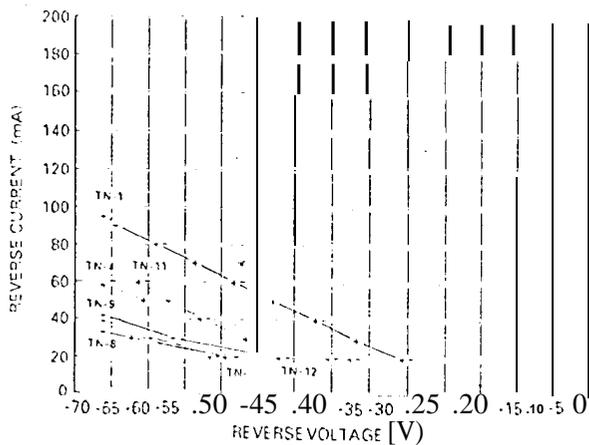


Fig. 6. Reverse bias characterization of boron diffusion thin BSFR silicon solar cells.

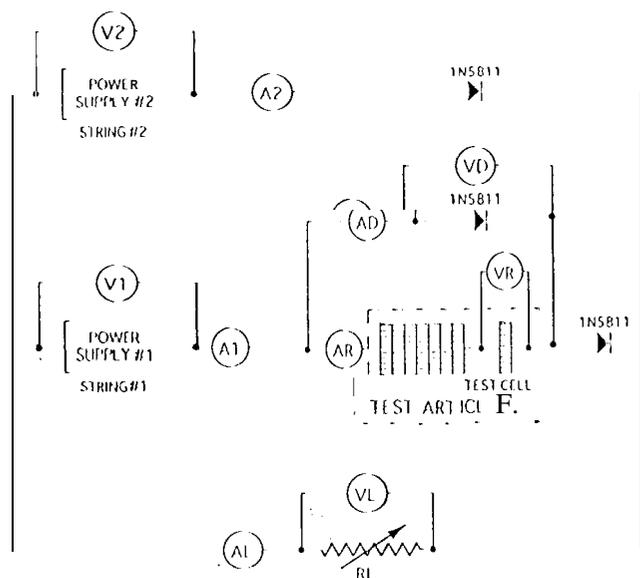
As part of the solar cell characterization activities, large area (0.5 x 2.4 cm), 380µm thick wafer diodes were obtained from a domestic supplier and characterized under forward and reverse conditions, at temperature, under long duration conditions and after charged particle irradiation. Thinner (~100 µm) wafer diodes were not readily available from domestic sources, but are being developed in limited quantity in Japan. These diodes, however, were not available for the APSA program.

A series of bench top circuit tests under ambient conditions were also performed to simulate diode-based cell modules containing each of the cell types with varying number of series cells. External cell circuits for higher voltage levels were simulated by a voltage supply.



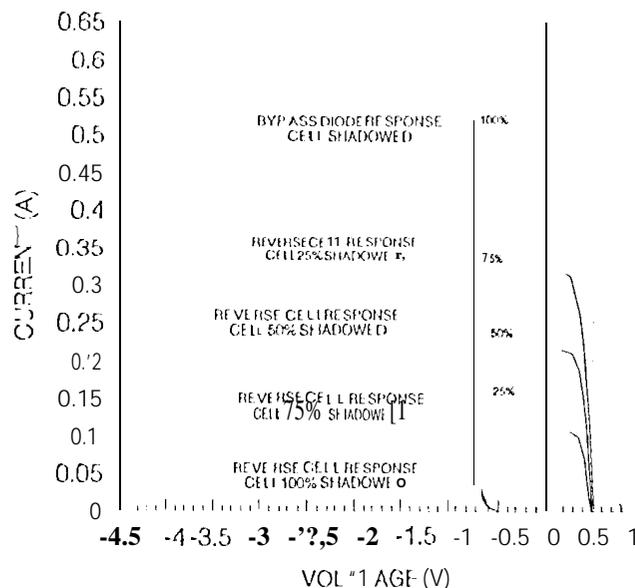
**Fig. 7** Reverse bias characteristics of boron ion-implanted thin silicon BSFR solar cells

Fig. 8 illustrates the test setup. Test results (Figs. 9 and 10) show a substantial difference in the diode/cell current sharing, for the two cell types as a function of shadow condition or simulated cell cracking condition. The boron ion-implanted BSFR silicon cell carries current essentially proportional to its illuminated area (i.e., a 100 percent shadowed cell results in all current bypassing the cell via the diode circuit). Whereas, for the boron diffusion BSFR silicon cell, the current sharing is sensitive to the actual reverse characteristics of the shadowed cell and the number of cells within the diode-bypassed circuit. Current sharing by the cell of 50 to 65 percent, respectively, was observed for a 100 percent shadowed cell when 8 and 11 series cells were diode-bypassed.

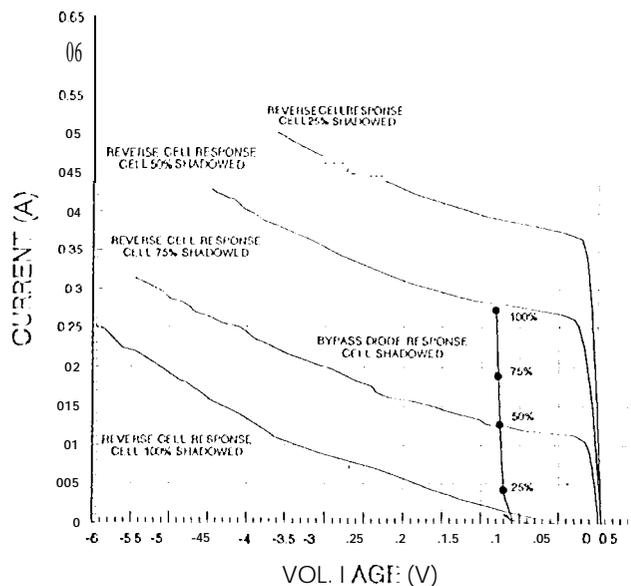


**Fig. 8.** Bypass circuit Test Set-IJp

The circuit test results correlate well with prior analyses done in 1991 and give confidence that the modeling of conditions beyond those tested will yield useful data for bypass circuit design. These test results, in conjunction with the solar cell and diode tests, are now being analyzed to develop guidelines for weight- and cost-effective circuit protection designs. This is being done as a function of solar cell reverse bias features, bus voltage level, heat conduction properties of the blanket substrate, and the degree of cell cracking or nature of cell/circuit shadowing.



**Fig. 9.** Current sharing between cell and bypass circuit for a 7-cell module of boron ion-implanted thin silicon cells as a function of one cell being shaded.



**Fig. 10.** Current sharing between cell and bypass circuit for an 8-cell module of boron diffusion thin silicon cells as a function of one cell being shaded.

## Prototype Wing Hardware Activities

Fig. 11 shows the 8-panel initial version of the deployed prototype wing. The prototype wing is representative of the 5.8 kW (BOI) wing except in six respects: (1) it is truncated in length, consisting of an 8-panel blanket assembly (3 m long), with two 3-panel units and two 1-panel leader panels, instead of a total of 42 panels; (2) the blanket substrate is 50  $\mu\text{m}$  carbon-loaded Kapton; (3) the blanket panels incorporate 14402 x 4 cm (instead of 2 x 5.7 cm) live thin silicon solar cell stacks (55  $\mu\text{m}$  cells, 50  $\mu\text{m}$  covers) soldered to the carrier to obtain a series of high voltage circuits ranging from 50 to 150 V (120 to 360 cells in series), with the rest of the panel area covered with mass-simulating aluminum blanks; (4) the live solar cell stacks are representations of flight-quality cells/covers (covers are uncoated etched glass rather than being AR/UV-coated and the cells are electrically active, although they do not necessarily possess high electrical performance characteristics); (5) there are no bypass diodes included in the solar cell circuits; and (6) construction is being done to standards consistent with the prototype nature of the hardware rather than to flight-quality standards.

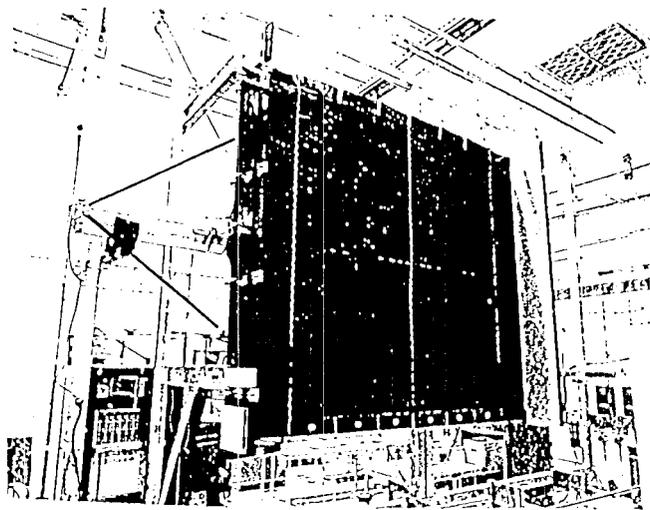


Fig. 11. Deployed 8-panel prototype wing.

The 8-panel version of the wing was subjected to a series of system-level tests whereby the stowed wing was exposed to acoustic and vibration conditions simulating the envelope of Shuttle and Atlas launch environments (Kurland, 1991). Stowed wing first mode natural frequency was about 34 Hz. In local areas of the blanket housing structure the vibration response g-loads reached 25 g's under a 10-g sine dwell base shake test. There was negligible change in the, 5200 Pa (0.75 psi) stowed blanket preload pressure. Deployment testing of the wing after exposure to these environments indicated that the preload/release mechanism operated smoothly and the blanket deployed in a controlled accordion-like fashion. Inspection of the primary structure revealed no damage.

After the two acoustic tests and eight vibration tests, about one percent of the live cells were cracked. All cell cracks were considered minor. Electrical continuity was maintained in all solar cell strings.

The wing was then modified under TRW discretionary funding to incorporate a full size germanium-coated, laminated Kapton/composite substrate in place of the inboard 3-panel unit, along with a blank inboard leader panel (Fig. 12). The 3-panel unit included about 1902 x 4 cm, 140  $\mu\text{m}$  thin GaAs/Ge cells and 1804 x 4 cm, 90  $\mu\text{m}$  thin GaAs/Ge cells, all with 150  $\mu\text{m}$  ceria-doped microsheet covers. The wing was subjected to simulated 10 g launch vibration testing and subsequent deployments. Only one additional silicon cell was cracked and about one percent of the GaAs/Ge cells cracked. All cell cracks were minor with no loss in electrical continuity. The use of edge-etched coverglass reduced the amount of coverglass damage.

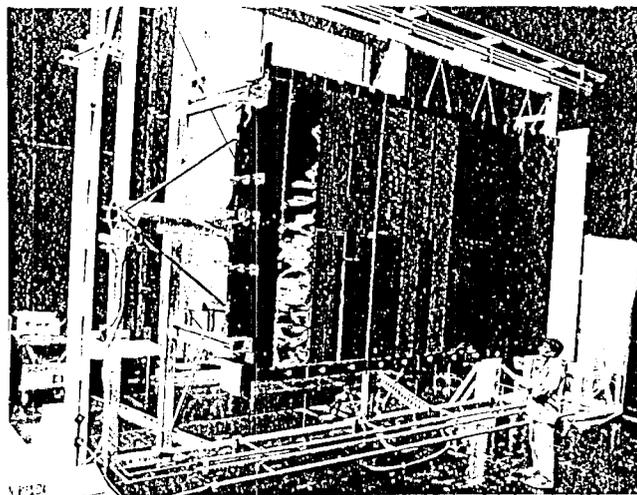


Fig. 12. Deployed 12-panel prototype wing

In conjunction with this latest version of the wing, a thermal cycle test panel was fabricated under TRW discretionary funding, consisting of the laminated substrate with thin (90 to 114  $\mu\text{m}$ ) 2x4 and 4x4 cm GaAs/Ge cells and two printed circuit harness segments representative of the blanket assembly harness. Thermal cycle testing representative of a LEO mission was initiated (-115 to +100°C). After about 25 percent of the planned 40,000 cycles, the power output has changed less than one percent. There was some cosmetic bowing in the substrate and wrinkling of the printed circuit harness segments.

About 300 GaAs/Ge cells were tested for reverse bias characteristics. The results indicated that shunt diodes would not be required for GaAs/Ge cells when incorporated into the laminated blanket substrate design, but probably would be required for a thin Kapton blanket design.

## Performance Estimates

Using thin BSFR silicon cells with a wafer diode every eight cells, the BOL specific power and power density are 138 W/kg and 140 W/m<sup>2</sup>, respectively, for a 5.8 kW BOL wing. BOL values (at 3.9 kW) are 92 W/kg and 94 W/m<sup>2</sup>, respectively, for a 10 year GEO mission. The use of 18 percent efficient, thin (~15 μm) GaAs/Ge cells provide about the same specific power trends as the less costly thin silicon cells over the range of 5 to 20 kW, even though the wing length would be reduced about 30 percent for comparable power levels. This is because the increased efficiency of the GaAs/Ge cell is offset by its density which is over twice that of silicon. The use of advanced thin film cells (a-Si, CIS), once their production maturity has been demonstrated, may improve specific power performance by 50 to 100 percent such that 200 W/kg (BOL) might be achievable within the next 10 years.

In progress are circuit analyses, based on the reported reverse bias testing, to ensure that electrical integrity of silicon solar cell blankets are maintained as the result of hot spots generated from cracked or shadowed cells. While the current design and performance estimates include an allocation for a wafer diode every eight cells, the recent cell and module tests indicate that design approach (i.e., the number of bypassed cells per diode) may be 100 conservative. Circuit protection guidelines may really depend on several factors, including: the nature of the cell reverse bias characteristics, the circuit voltage level, the nature of shadowing or the type/amount of cracked cells assumed. Thus, it is anticipated that the current APSA design and performance estimates will change to reflect updated circuit protection guidelines.

## APSA Applications

The transition of APSA from a testbed program to a flight hardware program has finally been achieved. A derivative of the APSA design was selected for the NASA/GSFC/FOS-AM solar array operating in a LEO polar mission. This one wing 5 kW (BOL) design will utilize 2.4 x 4.0 cm x 140 μm, 18 percent GaAs/Ge cells mounted on a germanium-coated Kapton/graphite laminated blanket. The blanket size will be about 5 m wide by 9 m long and consist of 24 cell-covered panels and one blank leader panel at each end. The total blanket assembly includes about 36480 cells with each 127 volt string having 190 series cells, without the need for shunt diodes. The blanket box structure and mechanism and mast system for FOS-AM will be a direct scale-up of the APSA design. Delivery of the first FOS-AM wing is scheduled for early 1996. Trade studies indicate the equivalent power level design using thin silicon cells would have resulted in a wing 50 percent larger in area at a cost about 10 percent more than the GaAs/Ge cell design.

Under near normal sun insolation the FOS-AM wing will have an estimated specific power performance of about 50 W/kg when considering the impact of mission-specific stiffness requirements and mechanical/electrical

interfaces, plus the fact that the blanket housing assembly, mast system and harnesses are being sized to include a power growth potential of 2.0 percent. Also, the wing is being designed to incorporate/support about 60 kg of additional components not considered under the generic APSA design. Nevertheless, the FOS-AM wing specific power performance is relatively high because of the pathfinder work done under the APSA program.

## Acknowledgment

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